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Dual Schmitt-Trigger Inverter

The NL27WZ14 is a high performance dual inverter with Schmitt–Trigger inputs operating from a 1.65 to 5.5 V supply.

Pin configuration and function are the same as the NL27WZ04, but the inputs have hysteresis and, with its Schmitt trigger function, the NL27WZ14 can be used as a line receiver which will receive slow input signals. The NL27WZ14 is capable of transforming slowly changing input signals into sharply defined, jitter–free output signals. In addition, it has a greater noise margin than conventional inverters. The NL27WZ14 has hysteresis between the positive–going and the negative–going input thresholds (typically 1 V) which is determined internally by transistor ratios and is essentially insensitive to temperature and supply voltage variations.

Features

- Designed for 1.65 V to 5.5 V V_{CC} Operation
- Over Voltage Tolerant Inputs and Outputs
- LVTTL Compatible Interface Capability with 5 V TTL Logic with $V_{CC} = 3 V$
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- Current Drive Capability is 24 mA at the Outputs
- Chip Complexity: FET = 72
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

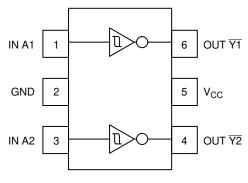
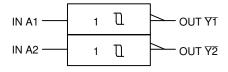


Figure 1. Pinout (Top View)

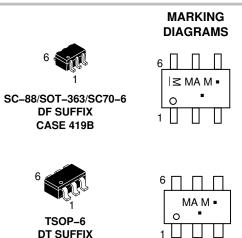






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M = Date Code* = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT

FIN ASSIGNMENT					
Pin	Function				
1	IN A1				
2	GND				
3	IN A2				
4	OUT Y2				
5	V _{CC}				
6	OUT YT				

FUNCTION TABLE

A Input	Y Output
L	Н
Н	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MAXIMUM RATINGS

Symbol	Characteristics	Value	Units
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
VI	DC Input Voltage	$-0.5 \leq V_l \leq +7.0$	V
Vo	DC Output Voltage, Output in HIGH or LOW State (Note 1)	$-0.5 \le V_O \le +7.0$	V
I _{IK}	DC Input Diode Current, V _I < GND	-50	mA
I _{OK}	DC Output Diode Current, V _O < GND	-50	mA
Ι _Ο	DC Output Sink Current	±50	mA
I _{CC}	DC Supply Current per Supply Pin	±100	mA
I _{GND}	DC Ground Current per Ground Pin	±100	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C
PD	Power Dissipation in Still Air; SC-88, TSOP-6	200	mW
θ_{JA}	Thermal Resistance; SC-88, TSOP-6	333	°C/W
TL	Lead Temperature, 1 mm from case for 10 s	260	°C
TJ	Junction Temperature under Bias	+150	°C
V _{ESD}	ESD Withstand Voltage Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 N/A	V
ILATCHUP	Latchup Performance Above V_{CC} and Below GND at 125°C (Note 5)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality Io absolute maximum rating must be observed.
 Tested to EIA/JESD22–A114–A

3. Tested to EIA/JESD22-A115-A

4. Tested to JESD22-C101-A

5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Units
V _{CC}	Supply Voltage Operating Data Retention Only	1.65 1.5	5.5 5.5	V
VI	Input Voltage	0	5.5	V
Vo	Output Voltage (High or LOW State)	0	5.5	V
T _A	Operating Free–Air Temperature	-55	+125	°C
Δt/ΔV	Input Transition Rise or Fall Rate $V_{CC} = 2.5 V \pm 0.2 V$ $V_{CC} = 3.0 V \pm 0.3 V$ $V_{CC} = 5.0 V \pm 0.5 V$	0 0 0	No Limit No Limit No Limit	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

ORDERING INFORMATION

Device	Package	Shipping [†]
NL27WZ14DFT2G	SC-88/SOT-363/SC70-6	3000 / Tape & Reel
NLV27WZ14DFT2G*	(Pb-Free)	SUUU / Tape & neer
NL27WZ14DTT1G	TSOP-6 (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	TA	= 25°C		–40°C ≤ T ₄	λ ≤ 85°C	–55°C ≤ T _A ≤ 125°C		
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Min	Max	Units
V _T +	Positive Input Threshold Voltage		2.3 2.7 3.0 4.5 5.5	1.0 1.2 1.3 1.9 2.2	1.5 1.7 1.9 2.7 3.3	1.8 2.0 2.2 3.1 3.6	1.0 1.2 1.3 1.9 2.2	1.8 2.0 2.2 3.1 3.6	1.0 1.2 1.3 1.9 2.2	1.8 2.0 2.2 3.1 3.6	V
V _T -	Negative Input Threshold Voltage		2.3 2.7 3.0 4.5 5.5	0.4 0.5 0.6 1.0 1.2	0.75 0.87 1.0 1.5 1.9	1.15 1.4 1.5 2.0 2.3	0.4 0.5 0.6 1.0 1.2	1.15 1.4 1.5 2.0 2.3	0.4 0.5 0.6 1.0 1.2	1.15 1.4 1.5 2.0 2.3	V
V _H	Input Hysteresis Voltage		2.3 2.7 3.0 4.5 5.5	0.25 0.3 0.4 0.6 0.7	0.75 0.83 0.93 1.2 1.4	1.1 1.15 1.2 1.5 1.7	0.25 0.3 0.4 0.6 0.7	1.1 1.15 1.2 1.5 1.7	0.25 0.3 0.4 0.6 0.7	1.1 1.15 1.2 1.5 1.7	V
V _{OH}	High–Level Output Voltage V _{IN} = V _{IH} or V _{IL}	$\begin{array}{l} I_{OH} = -100 \ \mu A \\ I_{OH} = -3 \ m A \\ I_{OH} = -8 \ m A \\ I_{OH} = -12 \ m A \\ I_{OH} = -16 \ m A \\ I_{OH} = -24 \ m A \\ I_{OH} = -32 \ m A \end{array}$	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5	$\begin{array}{c} V_{CC} = 0.1 \\ 1.29 \\ 1.9 \\ 2.2 \\ 2.4 \\ 2.3 \\ 3.8 \end{array}$	V _{CC} 1.52 2.1 2.4 2.7 2.5 4.0		V _{CC} - 0.1 1.29 1.9 2.2 2.4 2.3 3.8		V _{CC} - 0.1 1.29 1.8 2.1 2.3 2.2 3.7		V
V _{OL}	Low-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	$\begin{split} I_{OL} &= 100 \; \mu A \\ I_{OL} &= 4 \; m A \\ I_{OL} &= 8 \; m A \\ I_{OL} &= 12 \; m A \\ I_{OL} &= 16 \; m A \\ I_{OL} &= 24 \; m A \\ I_{OL} &= 32 \; m A \end{split}$	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5		0.08 0.2 0.22 0.28 0.38 0.42	0.1 0.24 0.3 0.4 0.4 0.55 0.55		0.1 0.24 0.3 0.4 0.4 0.55 0.55		0.1 0.24 0.4 0.5 0.5 0.55 0.65	V
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μA
I _{OFF}	Power Off Leakage Current	$V_{IN} = 5.5$ V or $V_{OUT} = 5.5$ V	0			1		10		10	μΑ
ICC	Quiescent Supply Current	V _{IN} = 5.5 V or GND	5.5			1		10		10	μΑ

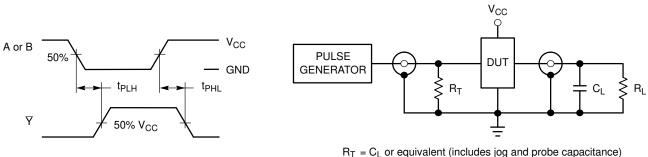
AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

				T _A = 25°C		$T_{A} = 25^{\circ}C \qquad -40^{\circ}C \le T_{A} \le 85^{\circ}C$		–55°C ≤ T _A ≤ 125°C			
Symbol	Parameter	Condition	V _{CC} (V)	Min	Тур	Max	Min	Max	Min	Max	Units
t _{PLH}	Propagation	$R_L = 1 M\Omega, C_L = 15 pF$	2.5 ± 0.2	1.8	4.3	7.4	1.8	8.1	1.8	9.1	ns
t _{PHL}	Delay Input A to Y (Figure 3 & 4)	$\label{eq:RL} \begin{array}{l} R_{L} = 1 \ M\Omega, \ C_{L} = 15 \ pF \\ R_{L} = 500 \ \Omega, \ C_{L} = 50 \ pF \end{array}$	3.3 ± 0.3	1.5 1.8	3.3 4.0	5.0 6.0	1.5 1.8	5.5 6.6	1.5 1.8	6.5 7.6	
	, ,	$\label{eq:RL} \begin{array}{l} R_{L} = 1 \ M\Omega, \ C_{L} = 15 \ pF \\ R_{L} = 500 \ \Omega, \ C_{L} = 50 \ pF \end{array}$	5.0 ± 0.5	1.0 1.2	2.7 3.2	4.1 4.9	1.0 1.2	4.5 5.4	1.0 1.2	5.5 6.4	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C _{IN}	Input Capacitance	V_{CC} = 5.5 V, V_{I} = 0 V or V_{CC}	2.5	pF
C _{PD}	Power Dissipation Capacitance (Note 6)	10 MHz, V_{CC} = 3.3 V, V_I = 0 V or V_{CC} 10 MHz, V_{CC} = 5.0 V, V_I = 0 V or V_{CC}	11 12.5	pF

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC} \bullet V_{CC}$.



 R_T = C_L or equivalent (includes jog and probe capacitance) R_T = Z_{OUT} of pulse generator (typically 50 $\Omega)$

Figure 3. Switching Waveforms

Figure 4. Test Circuit

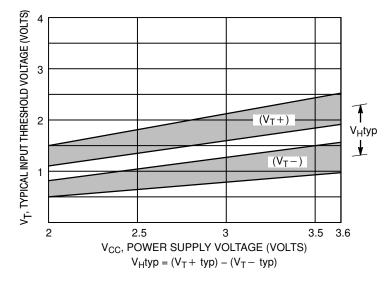


Figure 5. Typical Input Threshold, V_T+ , V_T- versus Power Supply Voltage

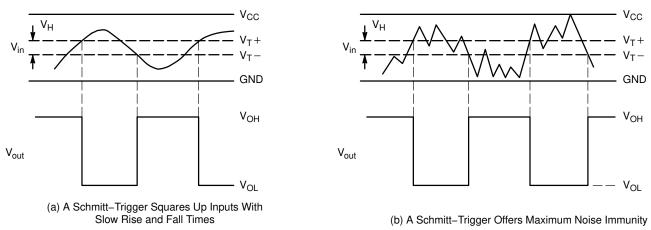
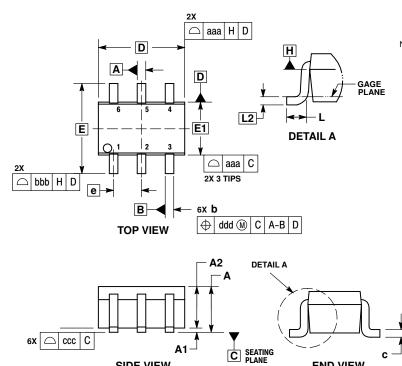


Figure 6. Typical Schmitt-Trigger Applications

NL27WZ14

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363 CASE 419B-02 **ISSUE Y**



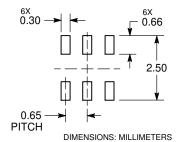
SIDE VIEW

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRU-SIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
 4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
 6. DIMENSIONS b AND C APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
 7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION & A MAXIMUM MATERIAL CONDI-TION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT. RADIUS OF THE FOOT.

	MILLIMETERS				INCHES	3	
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α			1.10			0.043	
A1	0.00		0.10	0.000		0.004	
A2	0.70	0.90	1.00	0.027	0.035	0.039	
σ	0.15	0.20	0.25	0.006	0.008	0.010	
c	0.08	0.15	0.22	0.003	0.006	0.009	
О	1.80	2.00	2.20	0.070	0.078	0.086	
Е	2.00	2.10	2.20	0.078	0.082	0.086	
E1	1.15	1.25	1.35	0.045	0.049	0.053	
e	().65 BS(0	0.026 BSC			
Г	0.26	0.36	0.46	0.010	0.014	0.018	
L2	0.15 BSC			0.006 BSC			
aaa	0.15			0.006			
bbb	0.30			0.012			
CCC	0.10			0.004			
ddd		0.10			0.004		

RECOMMENDED SOLDERING FOOTPRINT*

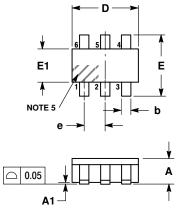
END VIEW

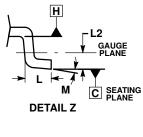


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSOP-6 CASE 318G-02 ISSUE V





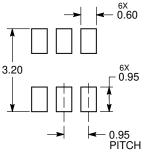


NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM 2
- 3.
- LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D 4. AND E1 ARE DETERMINED AT DATUM H. 5. PIN ONE INDICATOR MUST BE LOCATED IN THE INDICATED ZONE.

	MILLIMETERS					
DIM	MIN	NOM	MAX			
Α	0.90	1.00	1.10			
A1	0.01	0.06	0.10			
b	0.25	0.38	0.50			
С	0.10	0.18	0.26			
D	2.90	3.00	3.10			
E	2.50	2.75	3.00			
E1	1.30	1.50	1.70			
е	0.85	0.95	1.05			
Ĺ	0.20	0.40	0.60			
L2		0.25 BSC				
М	0°	-	10°			

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

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NL27WZ14/D